

Title (en)

METHOD FOR SELECTING FAULTY DIELECTRICS OF A SEMICONDUCTOR COMPONENT

Title (de)

VERFAHREN ZUM SELEKTIEREN FEHLERHAFTER DIELEKTRIKA EINES HALBLEITERBAUELEMENTES

Title (fr)

PROCEDE DE SELECTION DE DIELECTRIQUES DEFECTUEUX D'UN COMPOSANT A SEMI-CONDUCTEUR

Publication

EP 1438742 A2 20040721 (DE)

Application

EP 02776786 A 20021007

Priority

- DE 0203781 W 20021007
- DE 10149773 A 20011009

Abstract (en)

[origin: DE10149773A1] Process for selecting faulty dielectrics (2) of semiconductor component (1) comprises: forming a testing layer (3) during production of the component above dielectrics; simultaneously testing functionality of the dielectrics by applying electrical voltage on testing layer above and on substrate (4) below dielectrics; and removing or structuring testing layer to continue to production of component. Preferred Features: The testing layer is produced by intermediate structuring of the material layers already produced by the production process. The testing layer is made from polysilicon or polysilicon-germanium.

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IPC 8 full level

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